

# Jaewook Jeong

## List of Publications by Year in descending order

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papers

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times ranked

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#	ARTICLE	IF	CITATIONS
1	Fabrication and characterization of low-sheet-resistance and stable stretchable electrodes employing metal and metal nanowire hybrid structure. <i>Flexible and Printed Electronics</i> , 2021, 6, 045013.	2.7	0
2	Origin of performance improvement in solution-processed indium-gallium-zinc-oxide thin-film transistors having thin active layer and asymmetric dual gate structure. <i>AIP Advances</i> , 2020, 10, 125110.	1.3	1
3	Comparison of electrical performances of water and organic solvent-based amorphous indium-gallium-zinc-oxide thin-film transistors. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 101007.	1.5	1
4	Electrical Stability of Solution-Processed a-IGZO TFTs Exposed to High-Humidity Ambient for Long Periods. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 26-32.	2.1	18
5	Effects of helium annealing in low-temperature and solution-processed amorphous indium-gallium-zinc-oxide thin-film transistors. <i>AIP Advances</i> , 2019, 9, .	1.3	1
6	Electrical characterization of graphene source/drain electrodes in amorphous indium-gallium-zinc-oxide thin-film transistors subjected to plasma treatment in contact regions. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 071003.	1.5	2
7	Low-resistance stretchable electrodes using a thick silver layer and a PDMS-PDMS bonding technique. <i>AIP Advances</i> , 2019, 9, .	1.3	4
8	Short time helium annealing for solution-processed amorphous indium-gallium-zinc-oxide thin-film transistors. <i>AIP Advances</i> , 2018, 8, 085206.	1.3	8
9	Analysis of Plasma Treatment Effects on a Compliant Substrate for High Conductive, Stretchable Ag Nanowires. <i>Applied Science and Convergence Technology</i> , 2018, 27, 5-8.	0.9	1
10	Quantum-Mechanical Analysis of Amorphous Oxide-Based Thin-Film Transistors. <i>IEEE Journal of the Electron Devices Society</i> , 2017, 5, 182-187.	2.1	5
11	Accurate Defect Density-of-State Extraction Based on Back-Channel Surface Potential Measurement for Solution-Processed Metal-Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 1683-1688.	3.0	17
12	Simple active-layer patterning of solution-processed a-IGZO thin-film transistors using selective wetting method. <i>Current Applied Physics</i> , 2017, 17, 1727-1732.	2.4	5
13	Fabrication and characterization of stretchable copper electrodes on poly(dimethylsiloxane) substrate by direct deposition. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 115801.	1.5	6
14	Highly stretchable metallic silver electrodes on poly(dimethylsiloxane) substrate. <i>AIP Advances</i> , 2017, 7, .	1.3	2
15	Inert gas annealing effect in solution-processed amorphous indium-gallium-zinc-oxide thin-film transistors. <i>Journal of the Korean Physical Society</i> , 2017, 71, 209-214.	0.7	3
16	Effective mobility enhancement of amorphous In-Ga-Zn-O thin-film transistors by holographically generated periodic conductor. <i>AIP Advances</i> , 2016, 6, .	1.3	3
17	Storage-period dependent bias-stress instability of solution-processed amorphous indium-zinc-oxide thin-film transistors. <i>Current Applied Physics</i> , 2015, 15, S64-S68.	2.4	7
18	Gate voltage and drain current stress instabilities in amorphous In-Ga-Zn-O thin-film transistors with an asymmetric graphene electrode. <i>AIP Advances</i> , 2015, 5, 097141.	1.3	3

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19	Novel Gated-Multiprobe Method for Measuring a Back Electrode Effect in Amorphous Oxide-Based Thin-Film Transistors. IEEE Transactions on Electron Devices, 2014, 61, 3757-3761.	3.0	4
20	Physical characterization of amorphous In-Ga-Zn-O thin-film transistors with direct-contact asymmetric graphene electrode. AIP Advances, 2014, 4, 097111.	1.3	8
21	Oxygen Dispersive Diffusion Induced Bias Stress Instability in Thin Active Layer Amorphous In-Ga-Zn-O Thin-Film Transistors. Applied Physics Express, 2013, 6, 031101.	2.4	27
22	Electrical characterization of a-InGaZnO thin-film transistors with Cu source/drain electrodes. Applied Physics Letters, 2012, 100, 112109.	3.3	47
23	Intrinsic parameter extraction of a-InGaZnO thin-film transistors by a gated-four-probe method. Applied Physics Letters, 2012, 100, .	3.3	18
24	Scaling behaviour of a-IGZO TFTs with transparent a-IZO source/drain electrodes. Journal Physics D: Applied Physics, 2012, 45, 135103.	2.8	21
25	Debye Length and Active Layer Thickness-Dependent Performance Variations of Amorphous Oxide-Based TFTs. IEEE Transactions on Electron Devices, 2012, 59, 710-714.	3.0	62
26	Self-Defined Short Channel Formation With Micromolded Separator and Inkjet-Printed Source/Drain Electrodes in OTFTs. IEEE Electron Device Letters, 2011, 32, 1758-1760.	3.9	14
27	Inkjet-printed stretchable silver electrode on wave structured elastomeric substrate. Applied Physics Letters, 2011, 98, .	3.3	97
28	Paper 14: Investigation of TIPS-pentacene on Inkjet-Printed Silver Source/Drain Electrodes. Digest of Technical Papers SID International Symposium, 2011, 42, 1535-1538.	0.3	1
29	Stretchable Low Resistance Thick Silver Electrode on Poly(dimethylsiloxane) Compliant Elastomeric Substrate. Japanese Journal of Applied Physics, 2010, 49, 05EB09.	1.5	9
30	Substrate thermal conductivity effect on heat dissipation and lifetime improvement of organic light-emitting diodes. Applied Physics Letters, 2009, 94, .	3.3	97
31	MOSFET-Like Behavior of a-InGaZnO Thin-Film Transistors With Plasma-Exposed Source-Drain Bulk Region. Journal of Display Technology, 2009, 5, 495-500.	1.2	45
32	Modeling of Printed Wavy Edge Patterns in TFT Channel Area. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	1